

DIODE MODULE

DD(KD)30HB120/160

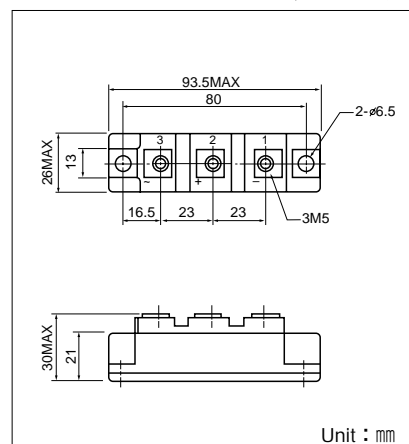
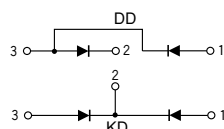
UL:E76102(M)

Power Diode Module **DD30HB** series are designed for various rectifier circuits. **DD30HB** has two diode chips connected in series and the mounting base is electrically isolated from elements for simple heatsink construction. Wide voltage rating up to, 1,600V is available for various input voltage.

- Isolated mounting base
- Two elements in a package for simple (single and three phase) bridge connections
- Highly reliable glass passivated chips
- High surge current capability

(Applications)

Various rectifiers, Battery chargers, DC motor drives



Maximum Ratings

(T_j=25°C unless otherwise specified)

| Symbol | Item | Ratings | | Unit |
|------------------|-------------------------------------|-----------|-----------|------|
| | | DD30HB120 | DD30HB160 | |
| V _{RRM} | Repetitive Peak Reverse Voltage | 1200 | 1600 | V |
| V _{RSM} | Non-Repetitive Peak Reverse Voltage | 1350 | 1700 | V |

| Symbol | Item | Conditions | Ratings | Unit |
|---------------------|--------------------------------------|--|-------------|------------------|
| I _{F(AV)} | Average Forward Current | Single phase, half wave, 180° conduction, T _c : 115°C | 30 | A |
| I _{F(RMS)} | R.M.S. Forward Current | Single phase, half wave, 180° conduction, T _c : 115°C | 47 | A |
| I _{FSM} | Surge Forward Current | 1/2 cycle, 50/60Hz, peak value, non-repetitive | 550/600 | A |
| I ² t | I ² t | Value for one cycle of surge current | 1500 | A ² S |
| T _J | Junction Temperature | | -40 to +150 | °C |
| T _{stg} | Storage Temperature | | -40 to +125 | °C |
| V _{ISO} | Isolation Breakdown Voltage (R.M.S.) | A.C.1minute | 2500 | V |
| Mounting Torque | Mounting (M6) | Recommended Value 2.5-3.9 (25-40) | 4.7 (48) | N·m (kgf·cm) |
| | Terminal (M5) | Recommended Value 1.5-2.5 (15-25) | 2.7 (28) | |
| | Mass | | 170 | g |

Electrical Characteristics

| Symbol | Item | Conditions | Ratings | Unit |
|----------------------|---------------------------------------|--|---------|------|
| I _{RRM} | Repetitive Peak Reverse Current, max. | at V _{DRM} , single phase, half wave. T _j =150°C | 10 | mA |
| V _{FM} | Forward Voltage Drop, max. | Forward current 90A, T _j =25°C, Inst. measurement | 1.50 | V |
| R _{th(j-c)} | Thermal Impedance, max. | Junction to case | 0.80 | °C/W |

